Philips Semiconductors

Product specification

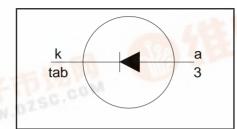
Rectifier diodes Schottky barrier

PBYR10100B series

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- · Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 60 \text{ V/ } 80 \text{ V/ } 100 \text{ V}$$
 $I_{F(AV)} = 10 \text{ A}$
 $V_F \le 0.7 \text{ V}$

GENERAL DESCRIPTION

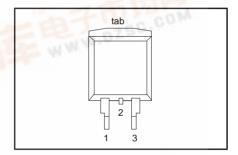
Schottky rectifier diodes in a plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR10100B series is supplied in the surface mounting SOT404 package.

PINNING

PIN	DESCRIPTION		
1	no connection		
2	cathode ¹		
3	anode		
tab	cathode		

SOT404



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	27	MAX.	0.00	UNIT
		PBYR10	-	60B	80B	100B	
V_{RRM}	Peak repetitive reverse voltage	AM GOLD.	-	60	80	100	V
V_{RWM}	Working peak reverse voltage	SC.COM	-	60	80	100	V
V_R	Continuous reverse voltage	T _{mb} ≤ 139 °C	-	60	80	100	V
I _{F(AV)}	Average rectified forward current	square wave; $\delta = 0.5$; $T_{mb} \le 133$ °C	-		10		А
I _{FRM}	Repetitive peak forward current	square wave; $\delta = 0.5$; $T_{mb} \le 133$ °C	-	_	20		Α
I _{FSM}	Non-repetitive peak forward current	t = 10 ms t = 8.3 ms sinusoidal; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RRM}(\text{max})}$		NWW	135 150		A A
I _{RRM}	Peak repetitive reverse surge current	pulse width and repetition rate limited by T _{i max}	-		1		Α
T _j	Operating junction temperature	SC.COM	-		150		°C
T_{stg}	Storage temperature		- 65		175		°C



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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb}	Thermal resistance junction			-	2	K/W
R _{th j-a}	to mounting base Thermal resistance junction to ambient	pcb mounted, minimum footprint, FR4 board	ı	50	-	K/W

ELECTRICAL CHARACTERISTICS

T_i = 25 °C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage	$I_{\rm F} = 10 \text{ A}; T_{\rm i} = 125 ^{\circ}\text{C}$	-	0.61	0.7	V
1		$I_{\rm F} = 20 \text{ A}; T_{\rm i} = 125 ^{\circ}\text{C}$	-	0.74	0.85	V
		$I_{\rm F} = 20 {\rm A}^{\prime}$	-	0.88	0.95	V
I _R	Reverse current	$\dot{V}_{R} = V_{RWM}$	-	5	150	μΑ
1		$V_R = V_{RWM}$; $T_i = 125^{\circ}C$	-	5	15	mΑ
C _d	Junction capacitance	$V_R = 5 \text{ W}; \text{ f} = 1 \text{ MHz}, T_j = 25 \text{ °C to } 125 \text{ °C}$	-	420	-	pF

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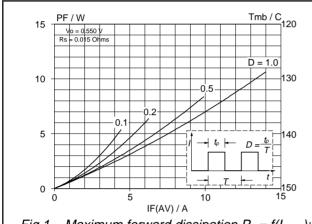


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

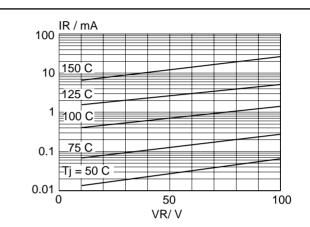


Fig.4. Typical reverse leakage current; $I_R = f(V_R)$; parameter T_j

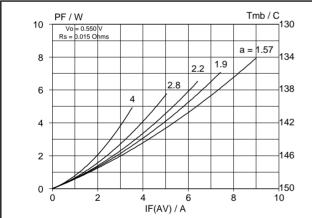


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$; sinusoidal current waveform where a = form factor $= I_{F(RMS)} / I_{F(AV)}$.

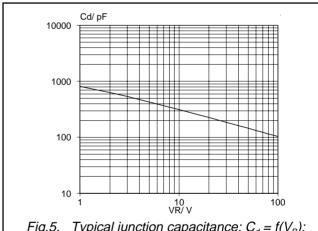


Fig.5. Typical junction capacitance; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25^{\circ}\text{C}$ to 125°C .

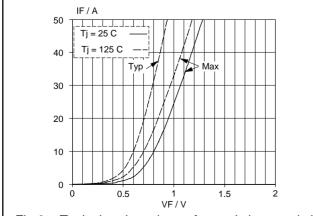


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

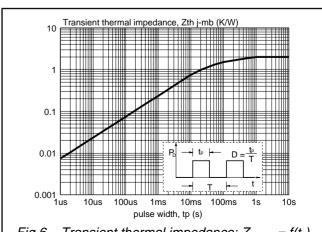
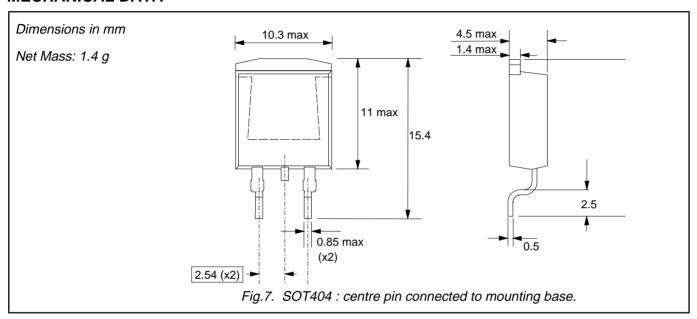


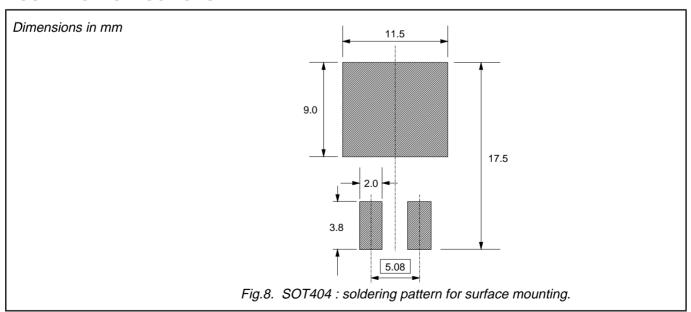
Fig.6. Transient thermal impedance; $Z_{th j-mb} = f(t_p)$.

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MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes
1. Epoxy meets UL94 V0 at 1/8".

Rectifier	diodes
Schottky	barrier

PBYR10100B series

DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
Limiting values				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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